



30V N-Channel Enhancement Mode MOSFET - ESD Protected

Voltage 30 V Current 0.6A

Features

- RDS(ON), VGS@4,5V, ID@0.6A<220mΩ
- RDS(ON), VGS@2.5V, ID@0.4A<290mΩ
- RDS(ON), VGS@1.8V, ID@0.1A<600mΩ
- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc.
- ESD Protected 2KV HBM
- Lead free in compliance with EU RoHS 2011/65/EU directive.
- Green molding compound as per IEC61249 Std. (Halogen Free)

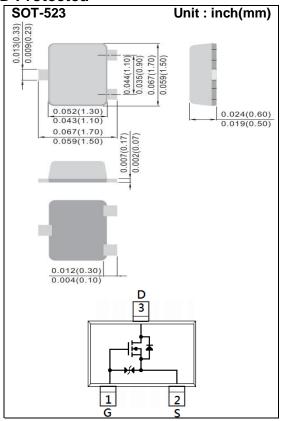
Mechanical Data

• Case: SOT-523 Package

Terminals: Solderable per MIL-STD-750, Method 2026

Approx. Weight: 0.00007 ounces, 0.002 grams

Marking: E04



Maximum Ratings and Thermal Characteristics (T_A=25 °C unless otherwise noted)

| PARAMETER | | SYMBOL | LIMIT | UNITS |
|---|----------------------|-----------------|------------|-------|
| Drain-Source Voltage | | V _{DS} | 30 | V |
| Gate-Source Voltage | | V_{GS} | <u>+</u> 8 | V |
| Continuous Drain Current | | I _D | 0.6 | Α |
| Pulsed Drain Current | | I _{DM} | 2.4 | Α |
| Power Dissipation | T _a =25°C | P _D | 300 | mW |
| | Derate above 25°C | | 2.4 | mW/°C |
| Operating Junction and Storage Temperature Range | | T_J, T_{STG} | -55~150 | °C |
| Typical Thermal resistance - Junction to Ambient (Note 3) | | $R_{	heta JA}$ | 417 | °C/W |





Electrical Characteristics (T_A=25 °C unless otherwise noted)

| PARAMETER | SYMBOL | TEST CONDITION | MIN. | TYP. | MAX. | UNITS | | |
|----------------------------------|---------------------|--|------|--------------|-------------|-------|--|--|
| Static | | | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V, I _D =250uA | 30 | - | - | V | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}=V_{GS}$, $I_{D}=250uA$ | 0.5 | 0.79 | 1.3 | V | | |
| Drain-Source On-State Resistance | R _{DS(on)} | V _{GS} =4.5V, I _D =0.6A | - | 177 | 220 | mΩ | | |
| | | V_{GS} =2.5V, I_{D} =0.4A | - | 223 | 290 | | | |
| | | V _{GS} =1.8V, I _D =0.1A | 1 | 330 | 600 | | | |
| Zero Gate Voltage Drain Current | I _{DSS} | V_{DS} =30V, V_{GS} =0V | - | 0.01 | 1 | uA | | |
| Gate-Source Leakage Current | I_{GSS} | $V_{GS}=\underline{+}8V, V_{DS}=0V$ | - | <u>+</u> 1.5 | <u>+</u> 10 | uA | | |
| Dynamic (Note 5) | | | | | | | | |
| Total Gate Charge | Q_g | V _{DS} =15V, I _D =0.6A, V _{GS} =4.5V ^(Note 1,2) | - | 1.5 | - | nC | | |
| Gate-Source Charge | Q_gs | | - | 0.3 | - | | | |
| Gate-Drain Charge | Q_gd | | - | 0.3 | - | | | |
| Input Capacitance | Ciss | \/ 45\/ \/ 0\/ | - | 93 | - | pF | | |
| Output Capacitance | Coss | V _{DS} =15V, V _{GS} =0V, f=1.0MHZ | - | 19 | - | | | |
| Reverse Transfer Capacitance | Crss | | - | 6 | - | | | |
| Turn-On Delay Time | td _(on) | V_{DD} =15V, I_{D} =0.6A, V_{GS} =4.5V, R_{G} =6 Ω (Note 1,2) | - | 6 | - | | | |
| Turn-On Rise Time | tr | | - | 33 | - | ns | | |
| Turn-Off Delay Time | td _(off) | | - | 37 | - | | | |
| Turn-Off Fall Time | tf | K _G =012 | - | 32 | - | | | |
| Drain-Source Diode | | | | | | | | |
| Maximum Continuous Drain-Source | | | | | 0.4 | А | | |
| Diode Forward Current | I _S | | | - | 0.4 | | | |
| Diode Forward Voltage | V_{SD} | I _S =1A, V _{GS} =0V | - | 0.81 | 1.2 | V | | |

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. R_{OJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper
- 4. The maximum current rating is package limited
- 5. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

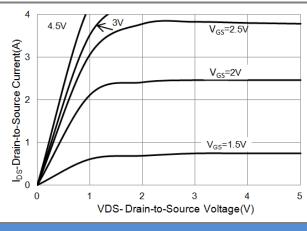


Fig.1 On-Region Characteristics

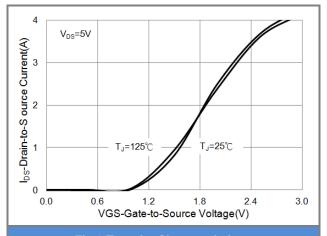


Fig.2 Transfer Characteristics

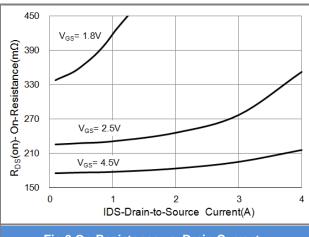


Fig.3 On-Resistance vs. Drain Current

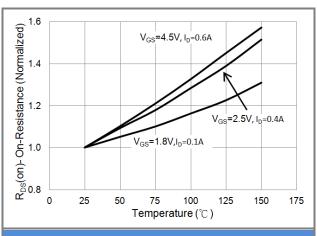
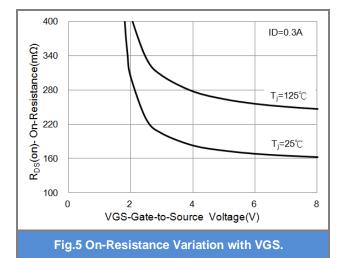
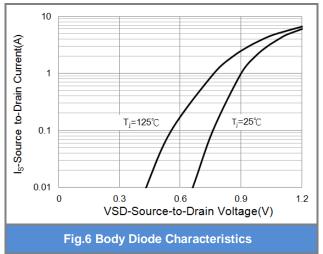


Fig.4 On-Resistance vs. Junction temperature









TYPICAL CHARACTERISTIC CURVES

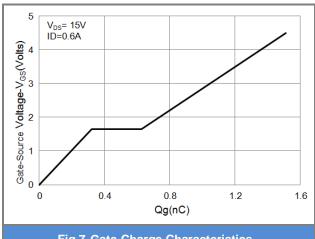


Fig.7 Gate-Charge Characteristics

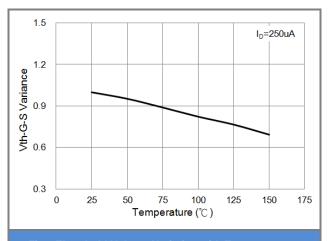


Fig.8 Threshold Voltage Variation with Temperature.

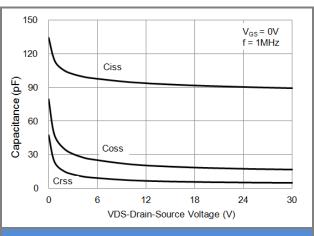


Fig.9 Capacitance vs. Drain-Source Voltage.

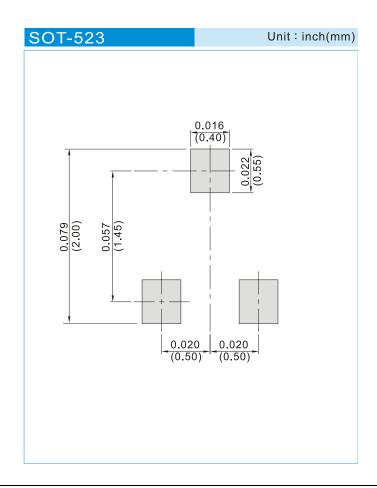




PART NO PACKING CODE VERSION

| Part No Packing Code | Package Type | Packing type | Marking | Version |
|----------------------|--------------|------------------|---------|--------------|
| PJE8404_R1_00001 | SOT-523 | 4K pcs / 7" reel | E04 | Halogen free |

MOUNTING PAD LAYOUT







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